Supporting Information

Polarization sensitive photodetector based on quasi-1D ZrSe₃

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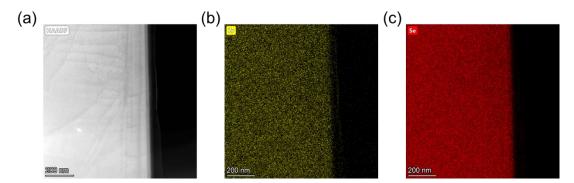


Fig. S1 (a) HAADF of quasi-ZrSe_{3.} (b, c) Zr and Se elemental mapping of quasi-1D ZrSe₃.

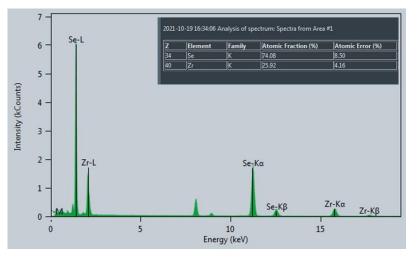


Fig. S2 TEM-EDX spectrum of quasi-1D ZrSe₃.

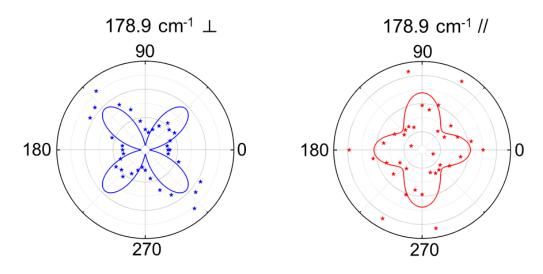


Fig. S3 Polar plots of angle-resolved and fitted peak intensities of 178.9 cm⁻¹.

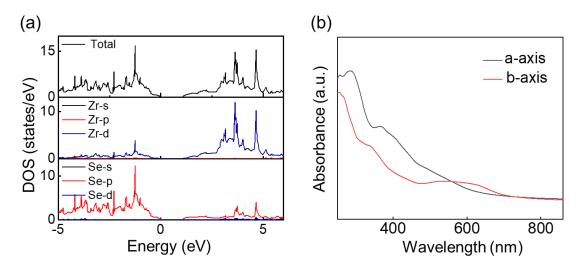


Fig. S4 (a) The total density of state and partial density of state for $ZrSe_3$. (b) The calculated absorption spectra along the a-axis and b-axis for $ZrSe_3$.

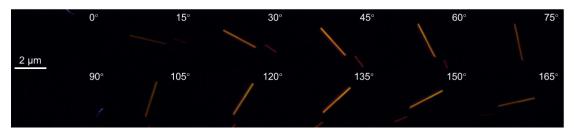


Fig. S5 Polarization-resolved optical microscope (PROM) images of quasi-1D $ZrSe_3$ with polarized direction varying from 0° to 165°.

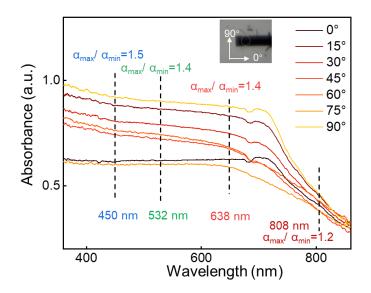


Fig. S6 Absorption spectra of quasi-1D $ZrSe_3$ under a beam of linearly polarized light, where the polarization direction varies from 0° to 90° .

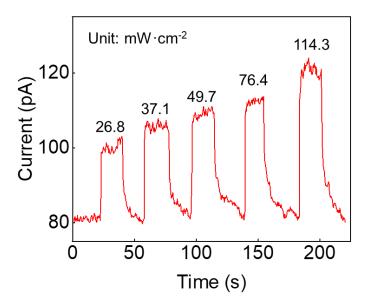


Fig. S7 Time-resolved photoresponse of the $ZrSe_3$ -based photodetector for a bias voltage of 5 V under 360 nm.

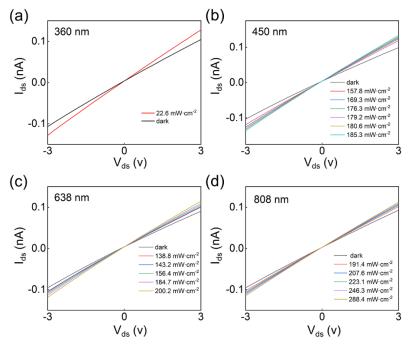


Fig. S8 *I*-*V* curves of ZrSe₃-based photodetectors in dark and light at 360, 450, 638, 808 nm.

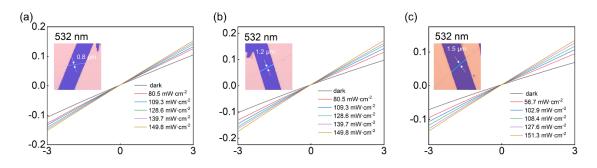


Fig. S9 *I*-*V* curves of ZrSe₃-based photodetector with width of (a) 0.8, (b) 1.2 and (c) 1.5 μ m at 532 nm.